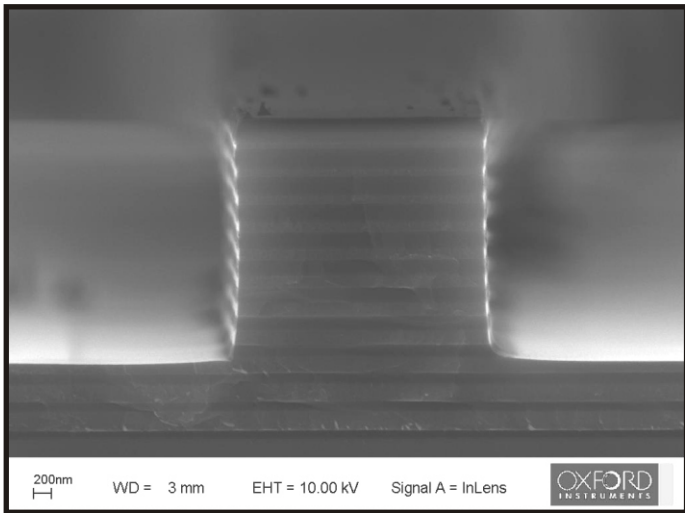
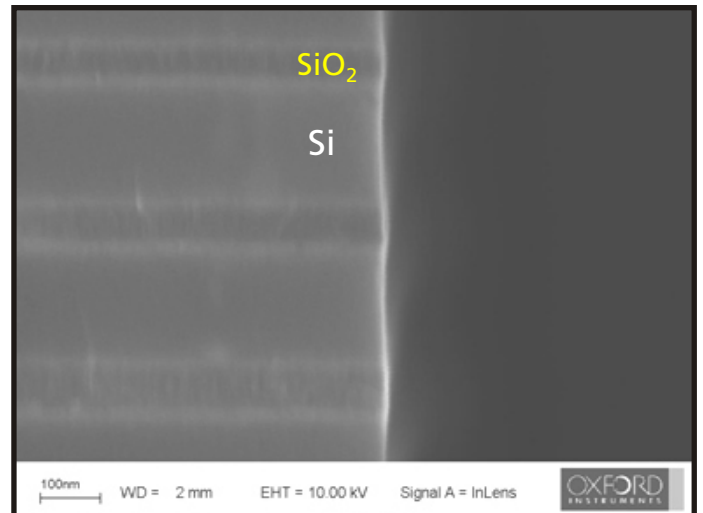


Plasmalab Data

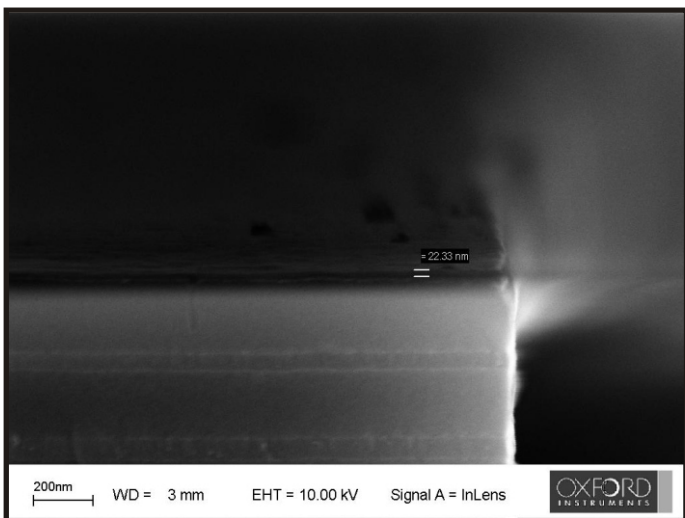
Smooth SiO₂-Si stack ICP etching



3µm SiO₂-Si stack etch, PR/Ni masking, ~90° profile



SiO₂-Si stack, side wall roughness / ripple < 6.7 nm



after 3µm stack etch, 22nm Ni mask remaining

Results:

- F-based chemistry
- single step process
- rate > 200 nm/ min
- selectivity to Ni mask > 100:1
- Sidewall roughness / ripple < 7 nm
- uniformity < +/- 5%

Systems:

- *Plasmalab 80Plus*
- *Plasmalab System 100*
- *Plasmalab System 133*

